

## **Amendments to the Claims**

Claims 1-77 (cancelled).

Claim 78 (previously presented): A method of forming a floating gate transistor comprising:

- forming an oxide-comprising layer against and physically contacting a semiconductive substrate;

- forming a first layer against and physically contacting the oxide-comprising layer, wherein the first layer comprises semiconductive material and a dopant, at least some of the dopant physically contacting the oxide-comprising layer;

- after forming the first layer, forming a second layer against and physically contacting the first layer, wherein the second layer comprises semiconductive material, the semiconductive material of the second layer having less dopant than the semiconductive material of the first layer;

- forming a third layer over the second layer, the third layer comprising dielectric material;

- forming a fourth layer over the third layer, the fourth layer comprising conductive material; and

- forming a floating gate transistor comprising the first, second, third, and fourth layers.

Claim 79 (previously presented): The method of claim 78 wherein the first and second layers comprise a floating gate having a thickness, and the forming of the first and second layers comprise forming the first layer to occupy at least 25 percent of the floating gate thickness.

Claim 80 (previously presented): The method of claim 78 wherein the first and second layers comprise a floating gate having a thickness, and the forming of the first and second layers comprise forming the first layer to occupy less than 75 percent of the floating gate thickness.

Claim 81 (previously presented): The method of claim 78 wherein the forming of the first layer comprises forming the first layer to have a dopant concentration of greater than or equal to about  $1 \times 10^{18} \text{cm}^{-3}$ .

Claim 82 (currently amended): The method of claim 78 wherein the forming of the first layer ~~comprises~~ comprises:

forming a polysilicon-comprising layer upon the oxide-comprising layer; and  
doping the polysilicon-comprising layer with phosphorous dopant material to a concentration of greater than or equal to about  $1 \times 10^{18} \text{cm}^{-3}$ .

Claim 83 (previously presented): The method of claim 82 wherein the doping the polysilicon-comprising layer is to a degree sufficient to define a sheet resistance of between 300 ohm/sq. and 400 ohm/sq.

Claim 84 (previously presented): The method of claim 78 wherein:

the first and second layers comprise a floating gate having a thickness, and the forming of the first and second layers comprise forming the first layer to occupy less than 75 percent of the floating gate thickness; and

the forming of the first layer comprises forming the first layer to have a dopant concentration of greater than or equal to about  $1 \times 10^{18} \text{cm}^{-3}$ .

Claim 85 (currently amended): The method of claim 78 wherein the ~~fourth~~ third layer comprises nitride.

Claim 86 (previously presented): The method of claim 78 wherein the first and second layers each have a thickness and the first and second layer thicknesses are substantially equal.

Claim 87 (previously presented): The method of claim 78 wherein the first and second layers each have a thickness and the first and second layer thicknesses are substantially different.

Claim 88 (previously presented): The method of claim 78 wherein a thickness of the first layer is less than about 550 Angstroms.

Claim 89 (previously presented): The method of claim 78 wherein a thickness of the first layer is between 450 Angstroms and 550 Angstroms.

Claim 90 (previously presented): The method of claim 78 wherein the second layer comprises undoped semiconductive material.